

USSN 10/040,328

PATENT

~~4~~**Drawings**

The applicants respectfully request the Examiner's approval of the new drawing of Figure 10 attached hereto. Support for the drawing of Figure 10 can be found in United States patent no. 6,537,513, which claims priority of Japanese patent application no. H9-306215, which was incorporated by reference in the application. Moreover, Figure 10 depicts the subject matter disclosed in paragraph [0072] of the application, namely, "[A] substrate structure composed of a layer of GaN deposited on a substrate can be used as a conductive substrate. Such substrate structure may additionally include a buffer layer of low-temperature-deposited nitride semiconductor material between the substrate and the layer of GaN".

The applicants respectfully submit that Figure 10 depicts subject matter verbally described in the application as filed and therefore adds no new matter to the application.